HIGH VOLTAGE POWER TRANSISTOR

The BU326 and BU326A Type are a fast switching high voltage transistor, more specially intended for operating in color TV receivers chopper supplies.

FEATURES:

Boca Semiconductor Corp. BSC

BU326A

NPN

BU326

* Collector-Emitter Sustaining Voltage -

6 AMPERE

V_{CEO(SUS)} = 375 V (Min.) - BU326 = 400 V (Min.) - BU326A

* Low Collector-Emitter Saturation Voltage -

 $V_{CE(sat)} = 1.5V (Max.)$ @ $I_C = 2.5 A$, $I_B = 0.5 A$

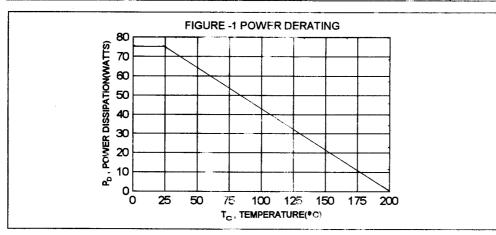
http://www.bocasemi.com

MAXIMUM RATINGS

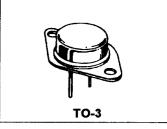
Characteristic	Symbol	BU326	BU326A	Unit
Collector-Emitter Voltage	V _{CEO}	375	400	V
Collector-Base Voltage	V _{CBO}	800 900		V
Emitter-Base Voltage	V _{EBO}	10		V
Collector Current - Continuous - Peak	lc	6.0 8.0		A
Base Current - Continuous	l _B	3.0		Α
Total Power Dissipation @T _C =25°C Derate above 25°C	P _D	75 0.428		w/°c
Operating and Storage Junction Temperature Range	T _J ,T _{STG}	- 65 to +200		°c

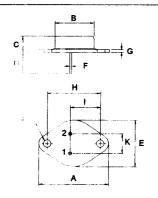
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	R⊕jc	2.33	°C/W









PIN 1.BASE 2.EMITTER COLLECTOR(CASE)

DIM	MILLIMETERS			
DIIVI	MIN	MAX		
Α	38.75	39.96		
В	19.28	22.23		
С	7.96	9.28		
D	11.18	12.19		
Ε	25.20	26.67		
F	0.92	1.09		
G	1.38	1.62		
Н	29.90	30.40		
1	16.64	17.30		
J	3.88	4.36		
K	10.67	11.18		

ELECTRICAL CHARACTERISTICS	T - 2500 unless otherwise noted \	
ELECTRICAL CHARACTERISTICS	(i c - 25 C uriless utileiwise noteu)	

Characteristic		Symbol	Min	Max	Unit		
OFF CHARACTERISTICS							
Collector - Emitter Sustaining Voltage (1) (I _C = 100 mA, I _B = 0)	BU326 BU326A	V _{CEO(SUS)}	375 400		V		
Collector Cutoff Current (V _{CE} = 800 V, V _{BE} = 0) (V _{CE} = 900 V, V _{BE} = 0)	BU326 BU326A	l _{CES}		1.0 1.0	mA		
Emitter Cutoff Current (V _{EB} = 10 V , I _C = 0)		I _{EBO}		10	mA		

ON CHARACTERISTICS (1)

DC Current Gain (I _C =1.0 A, V _{CE} = 5.0 V)	hFE	25(typ)		
Collector - Emitter Saturation Voltage (I _C =2.5 A, I _B = 0.5 A) (I _C =4.0 A, I _B = 1.25 A)	V _{CE(sat)}		1.5 3.0	٧
Base - Emitter Saturation Voltage (I _C =2.5 A, I _B = 0.5 A) (I _C =4.0 A, I _B = 1.25 A)	V _{BE(sat)}		1.4 1.6	٧

DYNAMIC CHARACTERISTICS

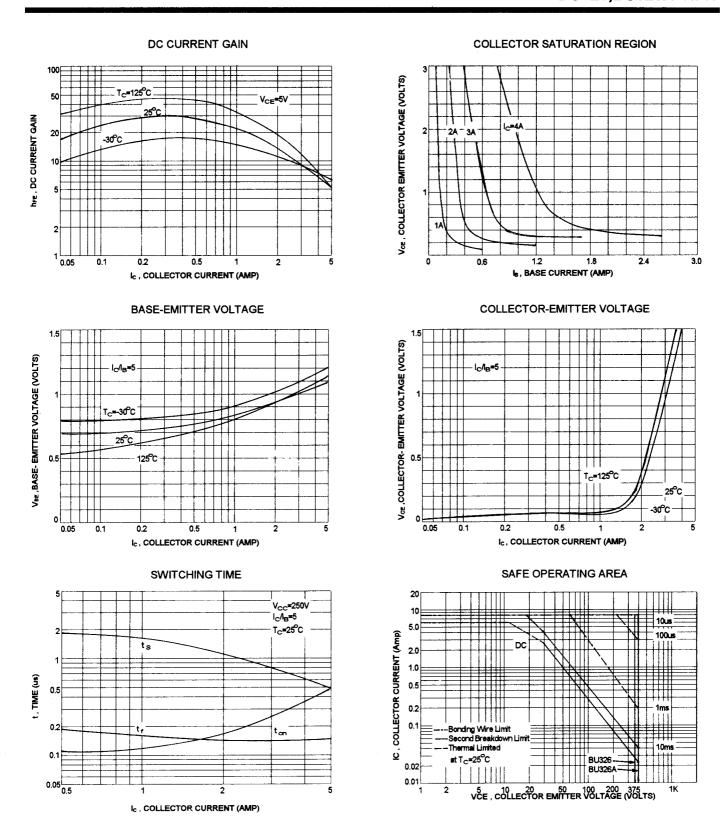
Current Gain - Bandwidth Product			MHz
$(I_C = 0.2 \text{ A}, V_{CE} = 10 \text{ V}, f = 1.0 \text{ MHz})$	f _T	4.0	

SWITCHING CHARACTERISTICS

Turn On Time	V _{CC} = 250 V, I _C = 2.5 A	ton	0.5	us
Storage Time	I _{B1} = 0.5 A,I _{B2} = -1 A	ts	3.5	us
Fall Time		t,	0.5	us

(1) Pulse Test: Pulse width \leq 300 us , Duty Cycle \leq 2.0%

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